

60 V, dual N-channel Trench MOSFET 15 June 2016

Product data sheet

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

| Table 1. Qui                            | ck reference data                |   |     |     |     |     |      |
|---|----------------------------------|---|-----|-----|-----|-----|------|
| Symbol                                  | Parameter                        | Conditions  |     | Min | Тур | Мах | Unit |
| Per transistor                          |                                  |   |     |     |     |     |      |
| V <sub>DS</sub>                         | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | 60  | V    |
| V <sub>GS</sub>                         | gate-source voltage              |   |     | -20 | -   | 20  | V    |
| I <sub>D</sub>                          | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                        | [1] | -   | -   | 170 | mA   |
| Static characteristics (per transistor) |                                  |   |     |     |     |     |      |
| R <sub>DSon</sub>                       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 25 °C |     | -   | 3   | 4.5 | Ω    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



## 5. Pinning information

| Table 2. | Pinning | information |                    |                    |
|----------|---------|-------------|--------------------|--------------------|
| Pin      | Symbol  | Description | Simplified outline | Graphic symbol     |
| 1        | S1      | source TR1  |                    | D1 D2              |
| 2        | G1      | gate TR1    |                    |                    |
| 3        | D2      | drain TR2   |                    |                    |
| 4        | S2      | source TR2  |                    |                    |
| 5        | G2      | gate TR2    | TSSOP6 (SOT363)    |                    |
| 6        | D1      | drain TR1   |                    | S1 S2<br>017aaa256 |

# 6. Ordering information

| Table 3. Ordering in | formation |  |         |
|----------------------|-----------|--|---------|
| Type number          | Package   |  |         |
|                      | Name      | Description                              | Version |
| NX138AKS             | TSSOP6    | plastic surface-mounted package; 6 leads | SOT363  |

## 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
|                        | [1]          |
| NX138AKS               | F8%          |

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

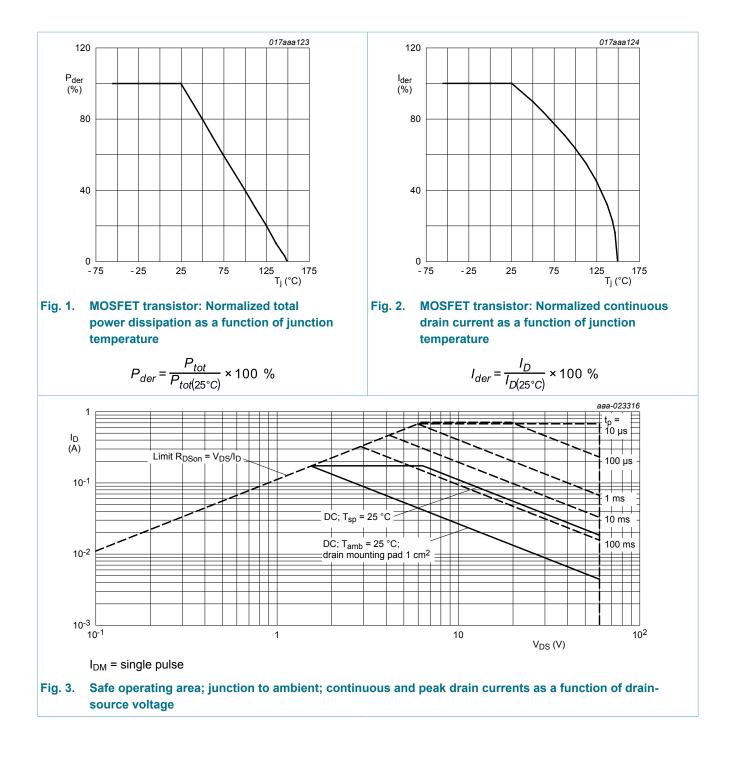
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                       | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------------------|-------------------------|---|-----|-----|------|------|
| Per transist                 | tor                     | · · · · · · · · · · · · · · · · · · ·                 |     |     |      |      |
| V <sub>DS</sub>              | drain-source voltage    | T <sub>j</sub> = 25 °C                                |     | -   | 60   | V    |
| V <sub>GS</sub>              | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub> drain current | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C      | [1] | -   | 170  | mA   |
|                              |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C     | [1] | -   | 110  | mA   |
| I <sub>DM</sub>              | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$ |     | -   | 680  | mA   |
| P <sub>tot</sub> total       | total power dissipation | T <sub>amb</sub> = 25 °C                              | [2] | -   | 265  | mW   |
|                              |                         |   | [1] | -   | 325  | mW   |
|                              |                         | T <sub>sp</sub> = 25 °C                               |     | -   | 1.33 | W    |
| Per device                   |                         | ·   |     | - 1 |      |      |
| Tj                           | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>             | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>             | storage temperature     |   |     | -65 | 150  | °C   |
| Source-dra                   | in diode                | 1   | 1   |     |      |      |
| Is                           | source current          | T <sub>amb</sub> = 25 °C                              | [1] | -   | 170  | mA   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 60 V, dual N-channel Trench MOSFET

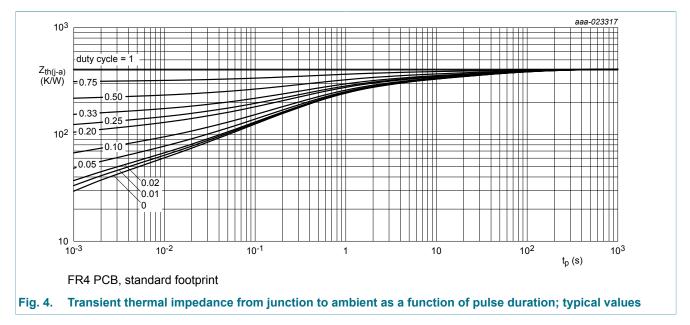


### 9. Thermal characteristics

| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| Per transis           | tor  |             | ·   |     |     |     |      |
| from j                | thermal resistance                                     | in free air | [1] | -   | 500 | 560 | K/W  |
|                       | from junction to ambient                               |             | [2] | -   | 450 | 480 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance<br>from junction to solder<br>point |             |     | -   | 100 | 115 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

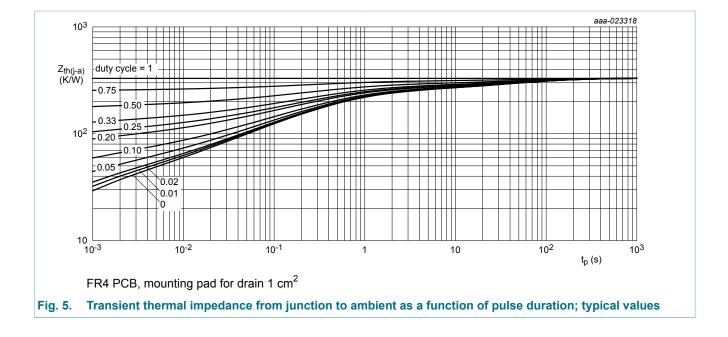
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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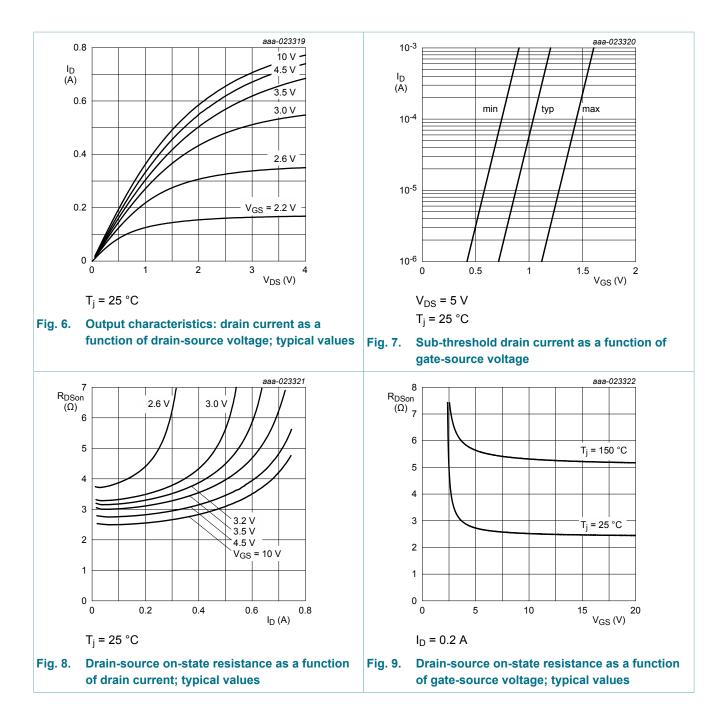
## **10. Characteristics**

| Symbol               | Parameter                         | Conditions   | Min | Тур | Max  | Unit |
|----------------------|-----------------------------------|--|-----|-----|------|------|
| Static chara         | cteristics (per transistor)       |  |     |     |      |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                      | 60  | -   | -    | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage     | I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C | 0.8 | 1.1 | 1.5  | V    |
| I <sub>DSS</sub>     | drain leakage current             | $V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                     | -   | -   | 1    | μA   |
| I <sub>GSS</sub>     | gate leakage current              | $V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                     | -   | -   | 2    | μA   |
|                      |                                   | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                    | -   | -   | -2   | μA   |
|                      |                                   | $V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                     | -   | -   | 0.5  | μA   |
|                      |                                   | $V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                    | -   | -   | -0.5 | μA   |
|                      |                                   | V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | -   | 100  | nA   |
|                      |                                   | $V_{GS}$ = -5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                     | -   | -   | -100 | nA   |
| R <sub>DSon</sub>    | drain-source on-state             | $V_{GS}$ = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 25 °C                   | -   | 3   | 4.5  | Ω    |
| resistance           | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 150 °C           | -   | 6   | 9    | Ω    |
|                      |                                   | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 150 mA; T <sub>j</sub> = 25 °C             | -   | 3.7 | 5.2  | Ω    |
|                      |                                   | V <sub>GS</sub> = 4 V; I <sub>D</sub> = 130 mA; T <sub>j</sub> = 25 °C             | -   | 4   | 6.3  | Ω    |
|                      |                                   | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 100 A; T <sub>j</sub> = 25 °C            | -   | 5   | 10   | Ω    |
| 9 <sub>fs</sub>      | forward<br>transconductance       | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 25 °C            | -   | 3.5 | -    | S    |
| Dynamic ch           | aracteristics (per transist       | or)  |     |     |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | $V_{DS}$ = 30 V; I <sub>D</sub> = 170 mA; V <sub>GS</sub> = 10 V;                  | -   | 0.9 | 1.4  | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 0.1 | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge                 |  | -   | 0.2 | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                          | -   | 15  | 20   | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 2.3 | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |  | -   | 1.5 | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS}$ = 30 V; I <sub>D</sub> = 170 mA; V <sub>GS</sub> = 10 V;                  | -   | 8   | 12   | ns   |
| t <sub>r</sub>       | rise time                         | R <sub>G(ext)</sub> = 75 Ω; T <sub>j</sub> = 25 °C                                 | -   | 10  | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               | 1 1  | -   | 8   | 20   | ns   |
| t <sub>f</sub>       | fall time                         | 1  | -   | 5   | -    | ns   |
| Source-drai          | n diode (per transistor)          | · · · · · · · · · · · · · · · · · · ·  | 1   | 1   |      |      |
| V <sub>SD</sub>      | source-drain voltage              | I <sub>S</sub> = 170 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C             | _   | 0.8 | 1.2  | V    |

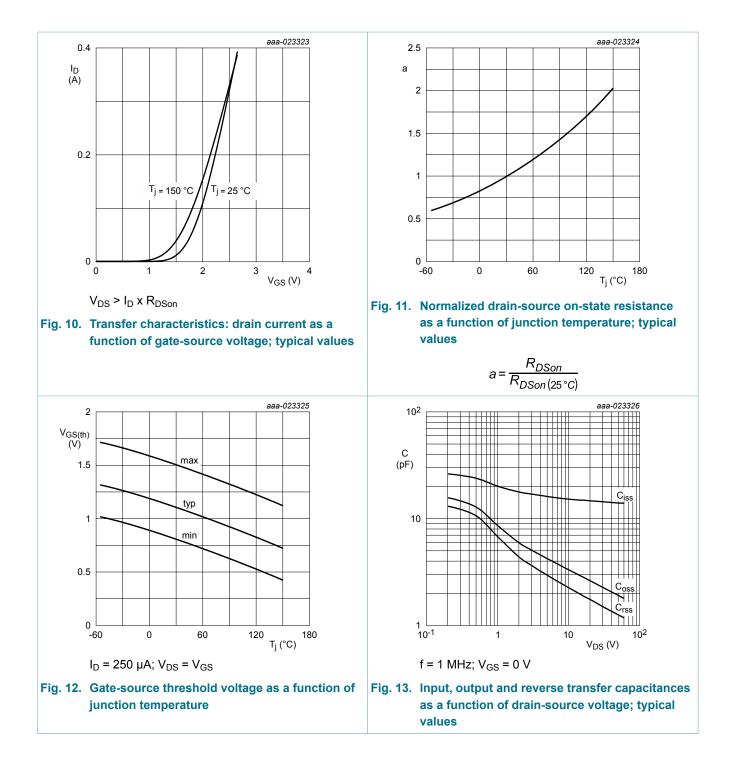
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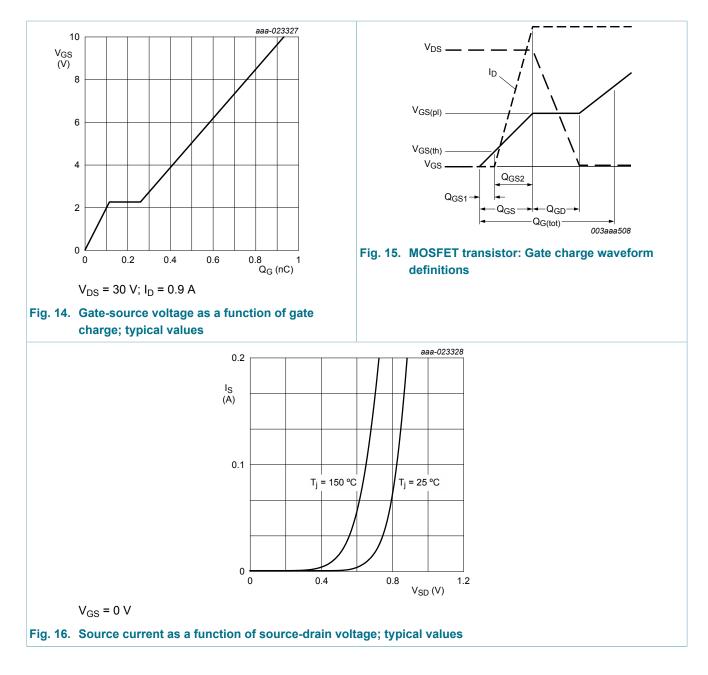
#### 60 V, dual N-channel Trench MOSFET



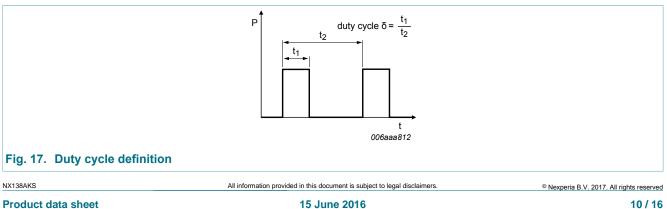
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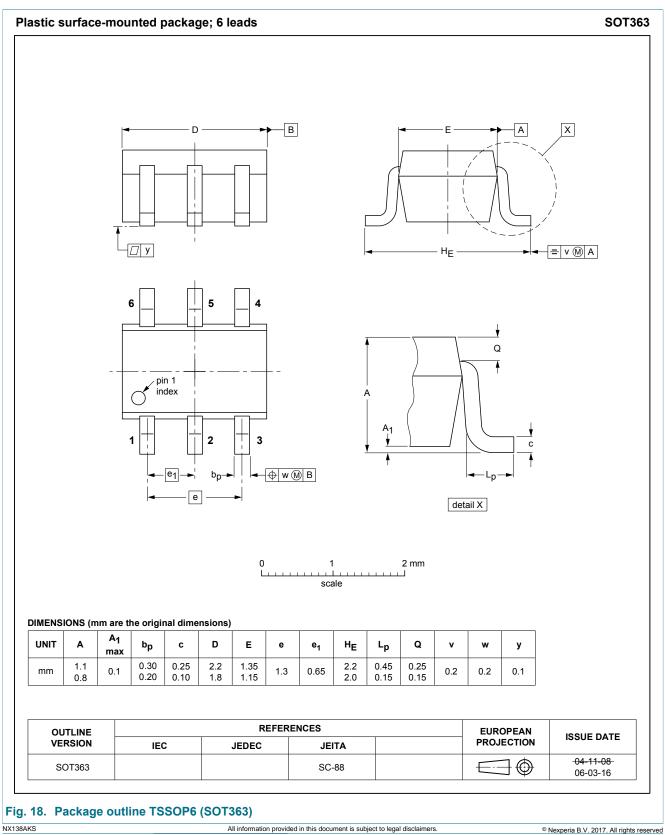
#### 60 V, dual N-channel Trench MOSFET



# 11. Test information

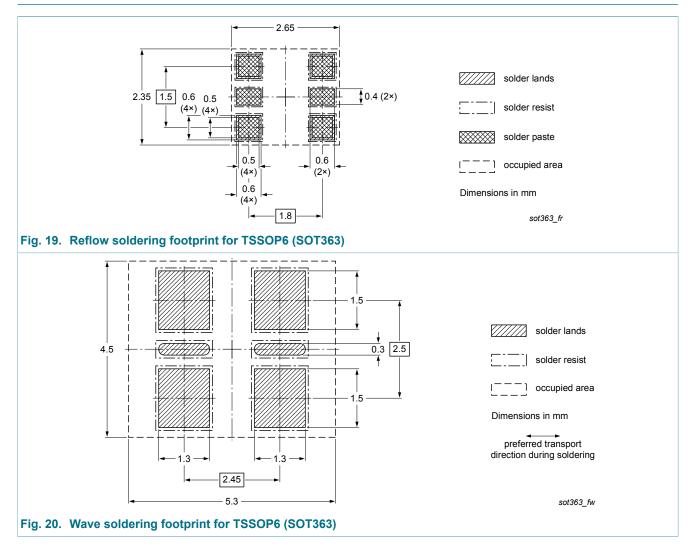


### 12. Package outline



#### 60 V, dual N-channel Trench MOSFET

### 13. Soldering



## 14. Revision history

| Table 8. Revision his | Table 8. Revision history |                    |               |            |  |  |  |
|-----------------------|---------------------------|--------------------|---------------|------------|--|--|--|
| Data sheet ID         | Release date              | Data sheet status  | Change notice | Supersedes |  |  |  |
| NX138AKS v.1          | 20160615                  | Product data sheet | -             | -          |  |  |  |

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| Document<br>status [1][2]            | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

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